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MITSUBISHI TRANSISTOR MODULES

QM75DY-2HB

HIGH POWER SWITCHING USE INSULATED TYPE

QM75DY-2HB



- **IC** Collector current **75A**
- **V_{CEX}** Collector-emitter voltage **1000V**
- **h_{FE}** DC current gain **750**
- **Insulated Type**
- **UL Recognized**

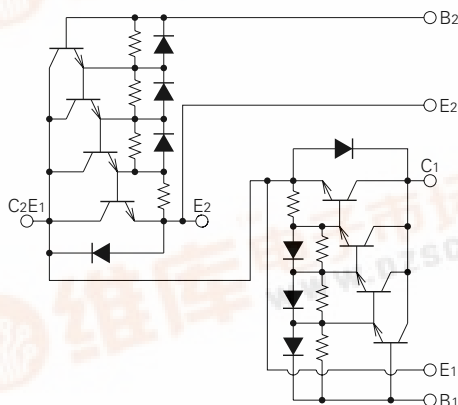
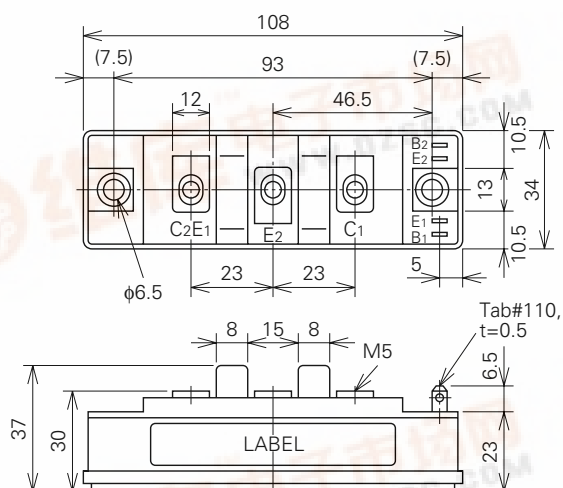
Yellow Card No. E80276 (N)
File No. E80271

APPLICATION

Inverters, Servo drives, UPS, DC motor controllers, NC equipment, Welders

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



QM75DY-2HB

HIGH POWER SWITCHING USE
INSULATED TYPE

ABSOLUTE MAXIMUM RATINGS (Tj=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
VCEX (SUS)	Collector-emitter voltage	IC=1A, VEB=2V	1000	V
VCEX	Collector-emitter voltage	VEB=2V	1000	V
VCBO	Collector-base voltage	Emitter open	1000	V
VEBO	Emitter-base voltage	Collector open	7	V
IC	Collector current	DC	75	A
-IC	Collector reverse current	DC (forward diode current)	75	A
PC	Collector dissipation	Tc=25°C	500	W
IB	Base current	DC	4	A
-ICSM	Surge collector reverse current (forward diode current)	Peak value of one cycle of 60Hz (half wave)	750	A
Tj	Junction temperature		-40~+150	°C
Tstg	Storage temperature		-40~+125	°C
Viso	Isolation voltage	Charged part to case, AC for 1 minute	2500	V
—	Mounting torque	Main terminal screw M5	1.47~1.96	N·m
			15~20	kg·cm
		Mounting screw M6	1.96~2.94	N·m
			20~30	kg·cm
—	Weight	Typical value	250	g

ELECTRICAL CHARACTERISTICS (Tj=25°C, unless otherwise noted)

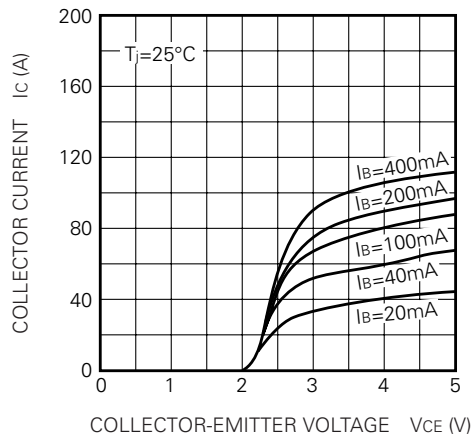
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
ICEX	Collector cutoff current	VCE=1000V, VEB=2V	—	—	2.0	mA
ICBO	Collector cutoff current	VCB=1000V, Emitter open	—	—	2.0	mA
IEBO	Emitter cutoff current	VEB=7V	—	—	50	mA
VCE (sat)	Collector-emitter saturation voltage	IC=75A, IB=100mA	—	—	4.0	V
VBE (sat)	Base-emitter saturation voltage		—	—	4.0	V
-VCEO	Collector-emitter reverse voltage	-IC=75A (diode forward voltage)	—	—	1.8	V
hFE	DC current gain	IC=75A, VCE=4V	750	—	—	—
ton	Switching time	VCC=600V, IC=75A, IB1=150mA, IB2=-1.5A	—	—	2.5	μs
ts			—	—	15	μs
tf			—	—	3.0	μs
Rth (j-c) O	Thermal resistance (junction to case)	Transistor part (per 1/2 module)	—	—	0.25	°C/W
Rth (j-c) R		Diode part (per 1/2 module)	—	—	1.2	°C/W
Rth (c-f)	Contact thermal resistance (case to fin)	Conductive grease applied (per 1/2 module)	—	—	0.13	°C/W

QM75DY-2HB

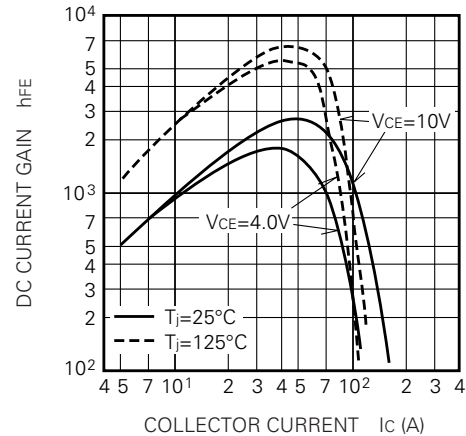
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

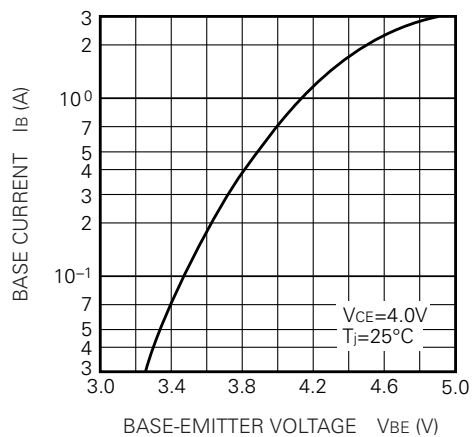
COMMON EMITTER OUTPUT
CHARACTERISTICS (TYPICAL)



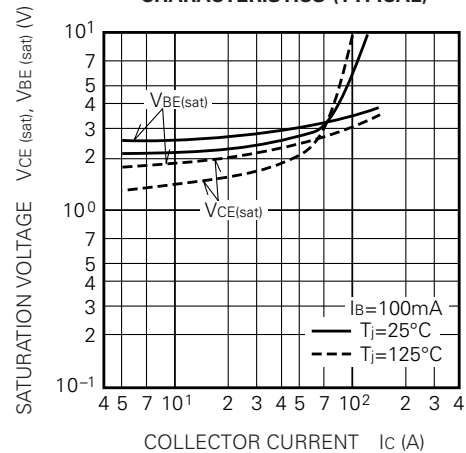
DC CURRENT GAIN VS.
COLLECTOR CURRENT (TYPICAL)



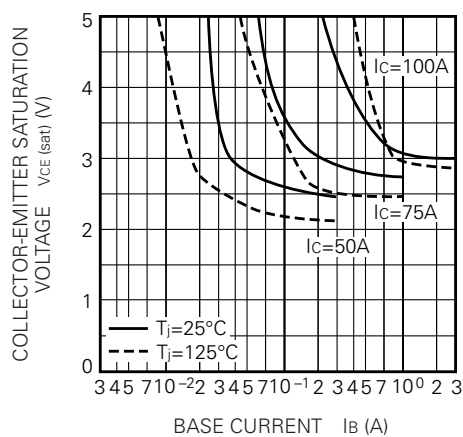
COMMON EMITTER INPUT
CHARACTERISTIC (TYPICAL)



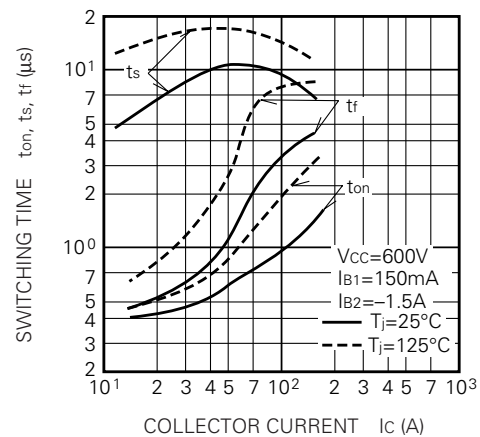
SATURATION VOLTAGE
CHARACTERISTICS (TYPICAL)



COLLECTOR-EMITTER SATURATION
VOLTAGE (TYPICAL)



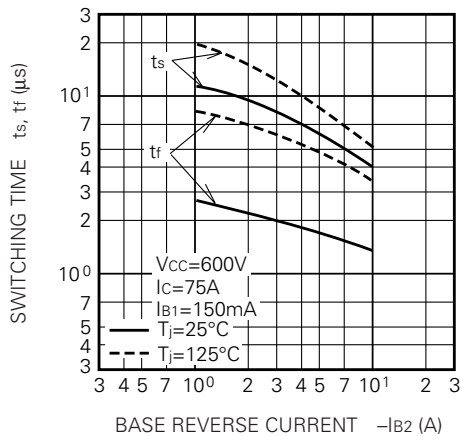
SWITCHING TIME VS. COLLECTOR
CURRENT (TYPICAL)



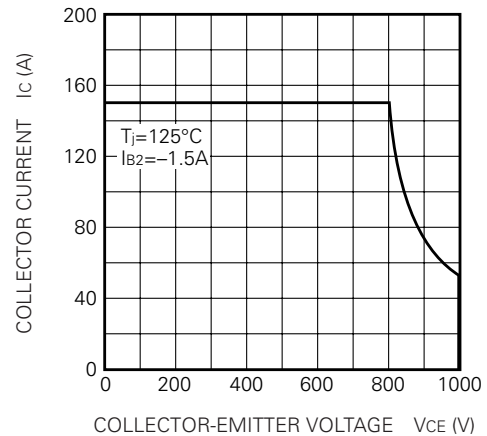
QM75DY-2HB

HIGH POWER SWITCHING USE
INSULATED TYPE

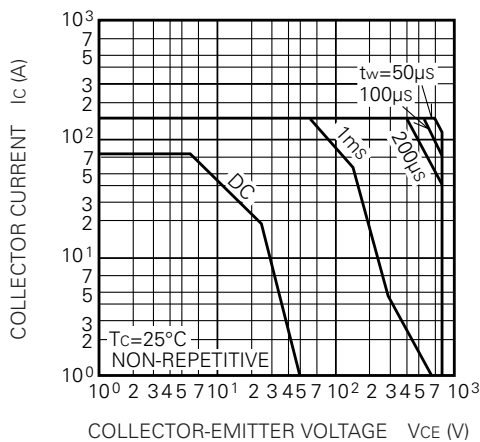
SWITCHING TIME VS. BASE
CURRENT (TYPICAL)



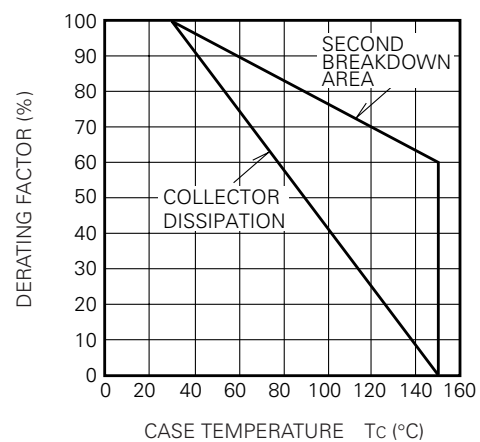
REVERSE BIAS SAFE OPERATING AREA



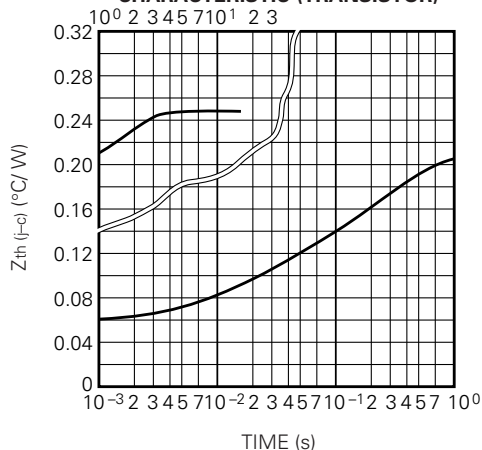
FORWARD BIAS SAFE OPERATING AREA



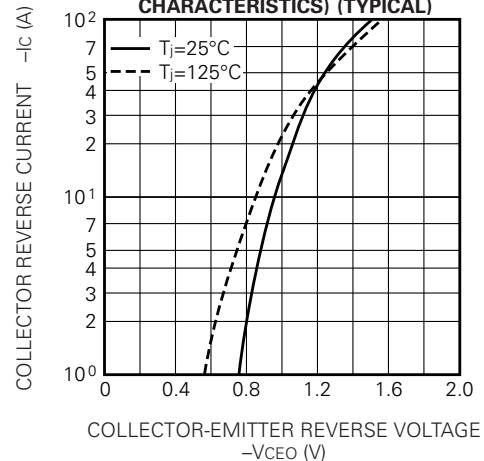
DERATING FACTOR OF F. B. S. O. A.



TRANSIENT THERMAL IMPEDANCE
CHARACTERISTIC (TRANSISTOR)



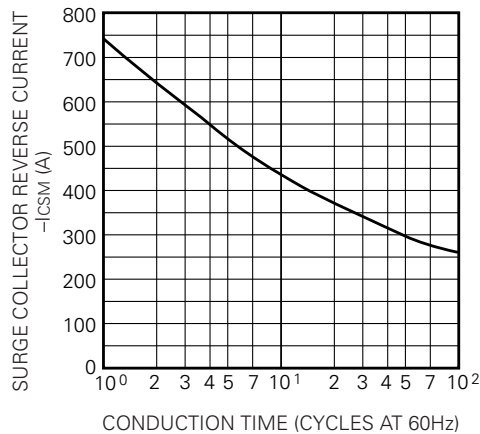
REVERSE COLLECTOR CURRENT VS.
COLLECTOR-EMITTER REVERSE
VOLTAGE (DIODE FORWARD
CHARACTERISTICS) (TYPICAL)



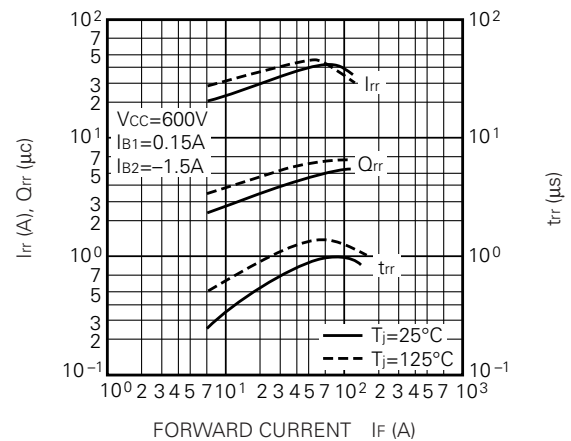
QM75DY-2HB

HIGH POWER SWITCHING USE
INSULATED TYPE

**RATED SURGE COLLECTOR REVERSE CURRENT
(DIODE FORWARD SURGE CURRENT)**



**REVERSE RECOVERY CHARACTERISTICS
OF FREE-WHEEL DIODE (TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE
CHARACTERISTIC (DIODE)**

